

PRODUCT FEATURES

- 650V IGBT³ CHIP(Trench+Field Stop technology)
- High short circuit capability,self limiting short circuit current
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Low switching losses



APPLICATIONS

- 3-Level-Applications
- Solar Applications
- UPS Systems

IGBT-inverter(T1、 T2、 T3、 T4)

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^{\circ}C$	650	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^{\circ}C$	150	A
		$T_C=25^{\circ}C$	150	
I_{CM}	Repetitive Peak Collector Current	$tp=1ms$	300	
P_{tot}	Power Dissipation Per IGBT		335	W

Diode-inverter(D1、 D2、 D3、 D4),Diode(D5、 D6)

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^{\circ}C$	650	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^{\circ}C$	150	A
I_{FRM}	Repetitive Peak Forward Current	$tp=1ms$	300	
I^2t		$T_J=125^{\circ}C, t=10ms, V_R=0V$	1800	A ² S

IGBT-inverter(T1、 T2、 T3、 T4)

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=2.4\text{mA}$	4.9	5.8	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=150\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.45	1.9	
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_J=150^\circ\text{C}$		1.7		
I_{CES}	Collector Leakage Current	$V_{CE}=650\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			1	mA
		$V_{CE}=650\text{V}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$			5	mA
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=25^\circ\text{C}$	-400		400	nA
R_{gint}	Integrated Gate Resistor			2		Ω
Q_g	Gate Charge	$V_{CE}=300\text{V}, I_C=150\text{A}, V_{GE}=\pm 15\text{V}$		1.6		μC
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		9.3		nF
C_{res}	Reverse Transfer Capacitance				290	
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=300\text{V}, I_C=150\text{A}$ $R_G=2.2\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		200	ns
			$T_J=150^\circ\text{C}$		210	ns
t_r	Rise Time	Inductive Load	$T_J=25^\circ\text{C}$		70	ns
			$T_J=150^\circ\text{C}$		80	ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=300\text{V}, I_C=150\text{A}$ $R_G=2.2\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		300	ns
			$T_J=150^\circ\text{C}$		330	ns
t_f	Fall Time	Inductive Load	$T_J=25^\circ\text{C}$		50	ns
			$T_J=150^\circ\text{C}$		70	ns
E_{on}	Turn on Energy	$V_{CC}=300\text{V}, I_C=150\text{A}$ $R_G=2.2\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		0.75	mJ
			$T_J=150^\circ\text{C}$		1.2	mJ
E_{off}	Turn off Energy	Inductive Load	$T_J=25^\circ\text{C}$		4	mJ
			$T_J=150^\circ\text{C}$		5.15	mJ
I_{sc}	Short Circuit Current	$t_{psc}\leq 6\mu\text{s}, V_{GE}=15\text{V}$ $T_J=125^\circ\text{C}, V_{CC}=360\text{V}$		750		A
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)			0.4	0.45	K /W

Diode-inverter(D1、 D2、 D3、 D4),Diode(D5、 D6)

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=150\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.55	1.95	V
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$		1.45		
t_{rr}	Reverse Recovery Time	$I_F=150\text{A}, V_R=300\text{V}$		210		ns
I_{RRM}	Max. Reverse Recovery Current	$dI_F/dt=-1600\text{A}/\mu\text{s}$		95		A
Q_{RR}	Reverse Recovery Charge	$T_J=150^\circ\text{C}$		11		μC
E_{rec}	Reverse Recovery Energy			3.5		mJ
R_{thJCD}	Junction to Case Thermal Resistance (Per Diode)				0.55	K /W

NTC CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
R_{25}	Resistance	$T_C=25^\circ\text{C}$		5		K Ω
$B_{25/50}$	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$			3375		K

MODULE CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		175	°C
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		> 200	
F	Mounting Force Per Clamp		40~80	N
Weight			50	g

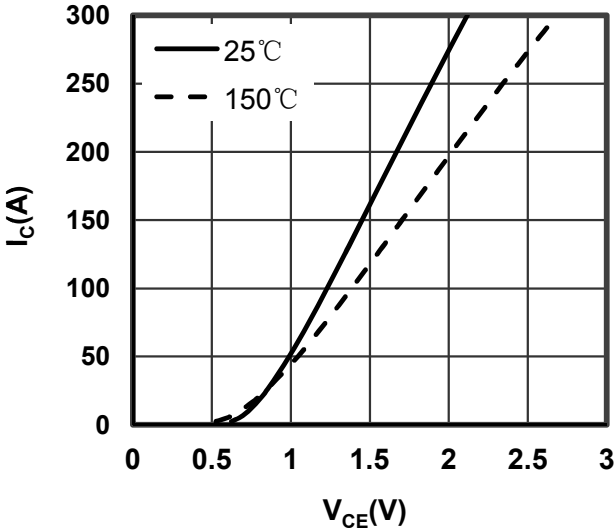


Figure 1. Typical Output Characteristics IGBT-inverter

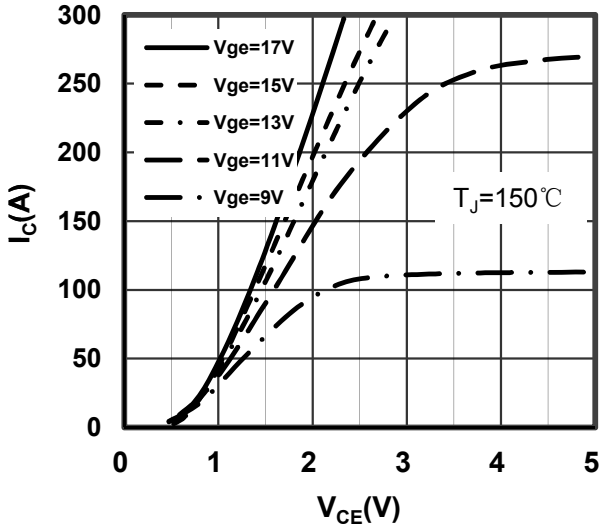


Figure 2. Typical Output Characteristics IGBT-inverter

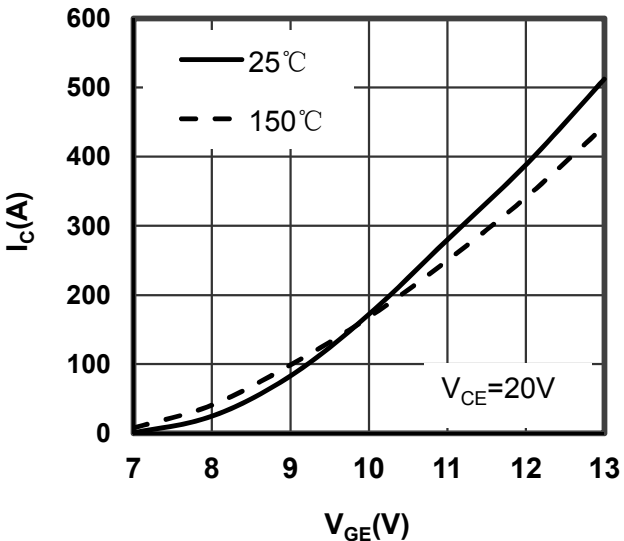


Figure 3. Typical Transfer characteristics IGBT-inverter

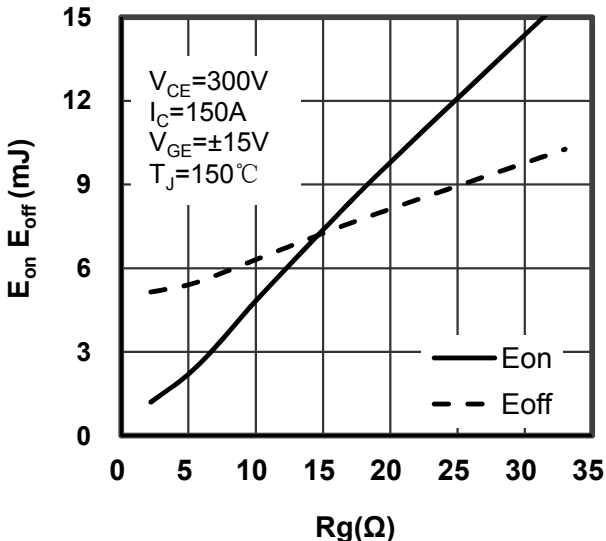


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

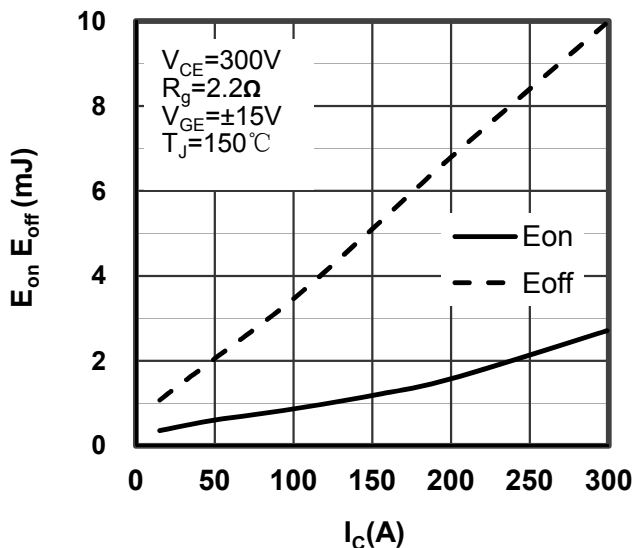


Figure 5. Switching Energy vs Collector Current IGBT-inverter

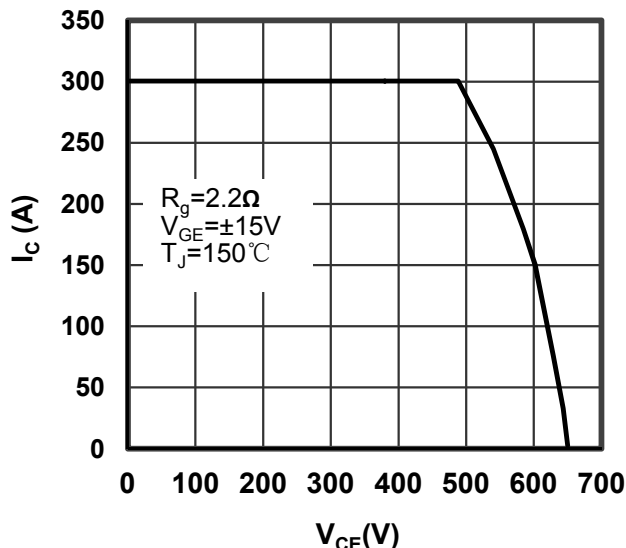


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

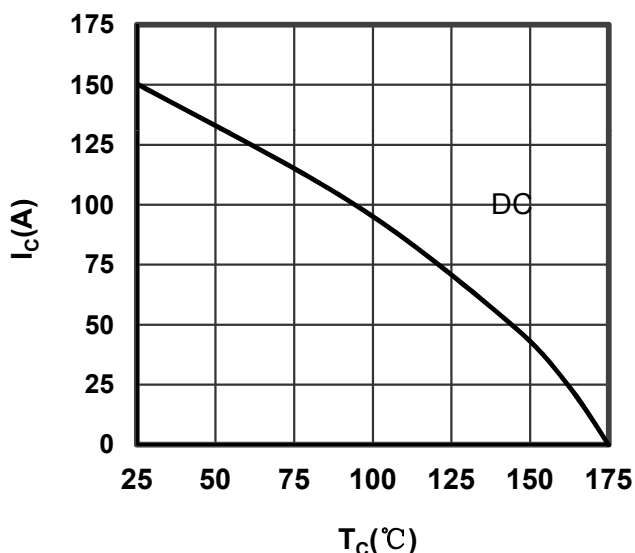


Figure 7. Collector Current vs Case temperature IGBT -inverter

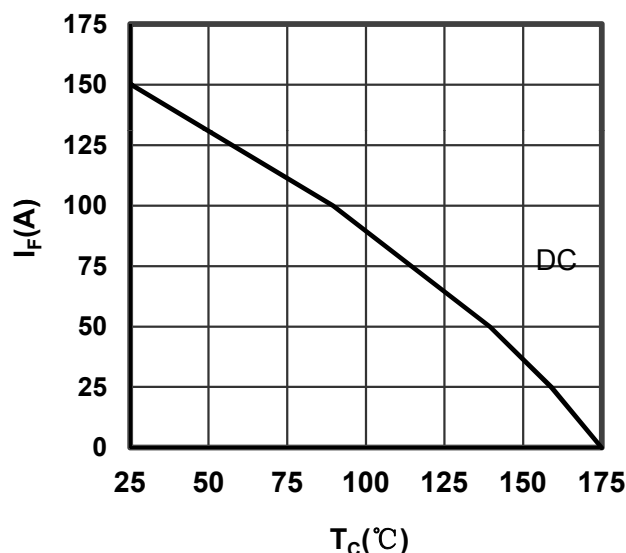


Figure 8. Forward current vs Case temperature Diode -inverter

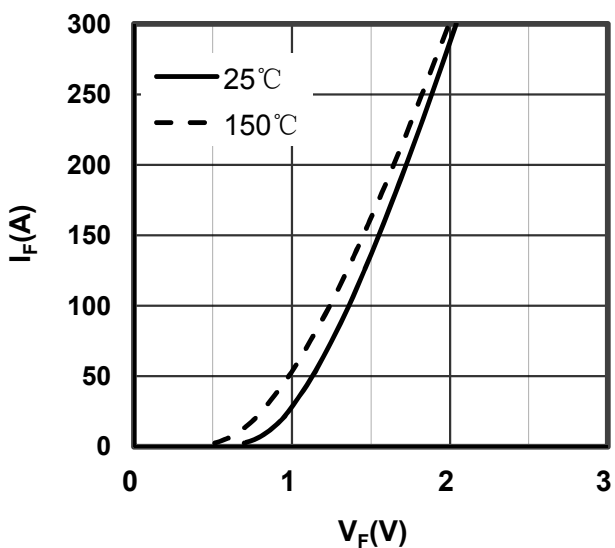


Figure 9. Diode Forward Characteristics Diode -inverter

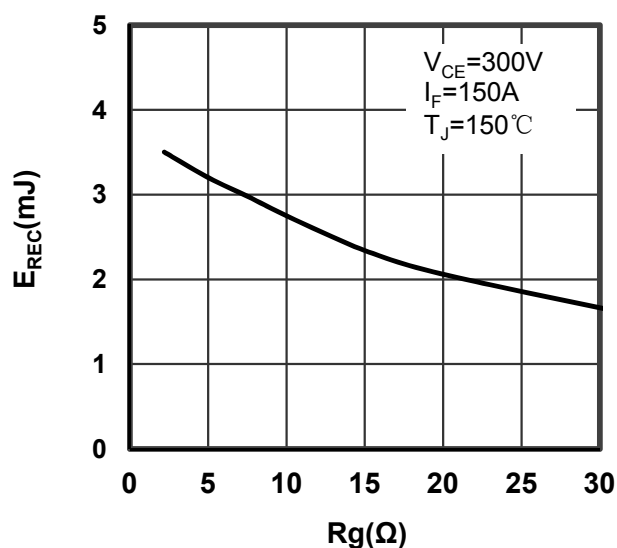


Figure 10. Switching Energy vs Gate Resistor Diode -inverter

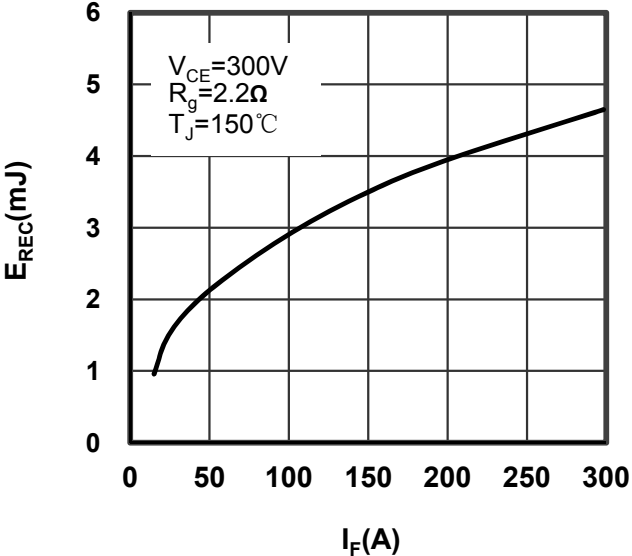


Figure 11. Switching Energy vs Forward Current Diode-inverter

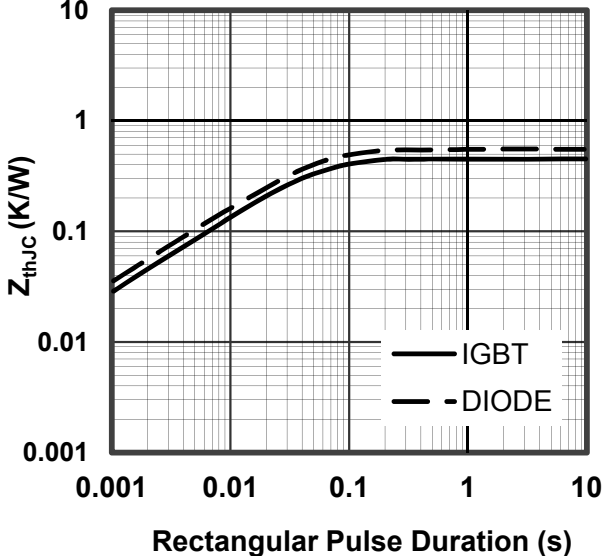


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

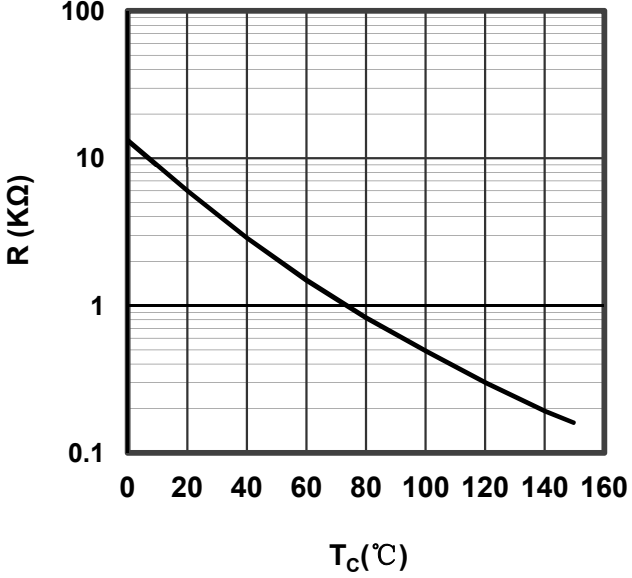


Figure 13. NTC Characteristics

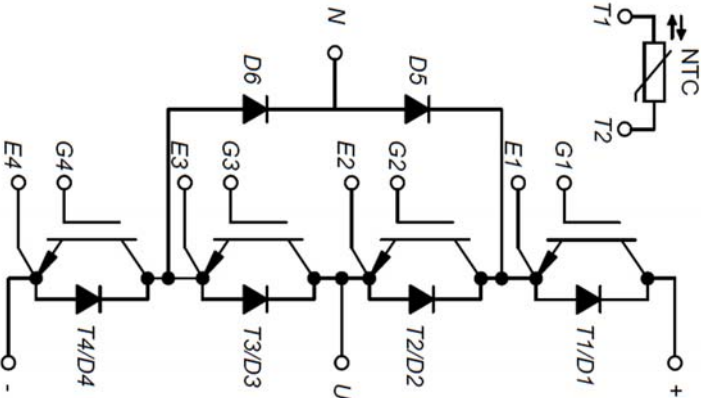
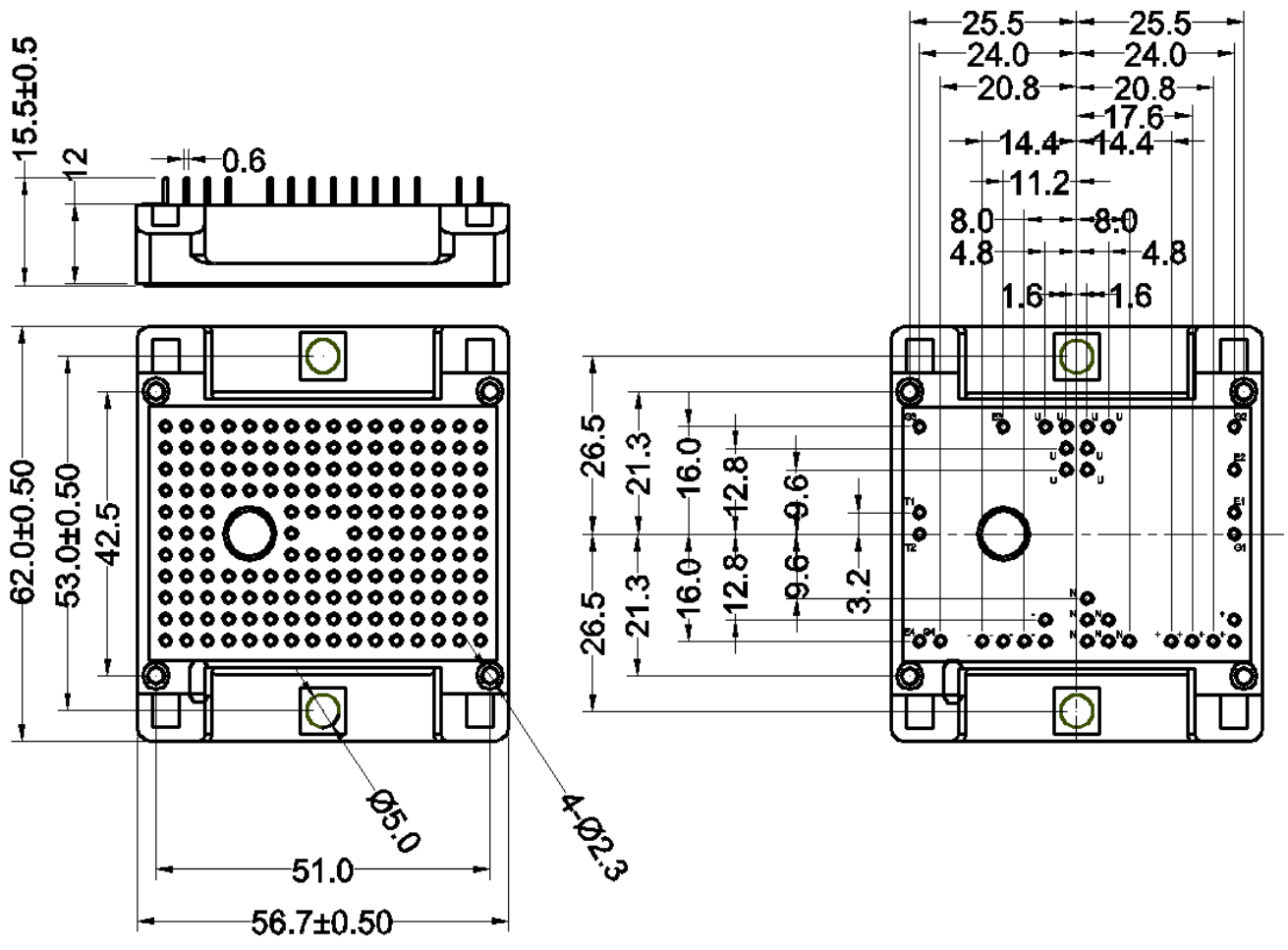


Figure 14. Circuit Diagram



Dimensions in (mm)
 Figure 15. Package Outline